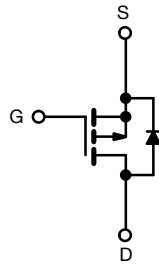


Power MOSFET

TO-220AB


P-Channel MOSFET

FEATURES

- Dynamic dV/dt rating
- P-channel
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

PRODUCT SUMMARY

V_{DS} (V)	-200	
$R_{DS(on)}$ (Ω)	$V_{GS} = -10$ V	1.5
Q_g max. (nC)	22	
Q_{gs} (nC)	12	
Q_{gd} (nC)	10	
Configuration	Single	

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRF9620PbF
Lead (Pb)-free and halogen-free	IRF9620PbF-BE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)



PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	-200	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	V_{GS} at -10 V	A
		$T_C = 25^\circ\text{C}$	
		$T_C = 100^\circ\text{C}$	-2.0
Pulsed drain current ^a	I_{DM}	-14	
Linear derating factor		0.32	W/ $^\circ\text{C}$
Maximum power dissipation	P_D	40	W
Peak diode recovery dV/dt ^b	dV/dt	-5.0	V/ns
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Soldering recommendations (peak temperature) ^c	For 10 s	300	
Mounting torque	6-32 or M3 screw	10	
		1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $I_{SD} \leq -3.5$ A, $dI/dt \leq 95$ A/ μs , $V_{DD} \leq V_{DS}$, $T_J \leq 150^\circ\text{C}$
- 1.6 mm from case



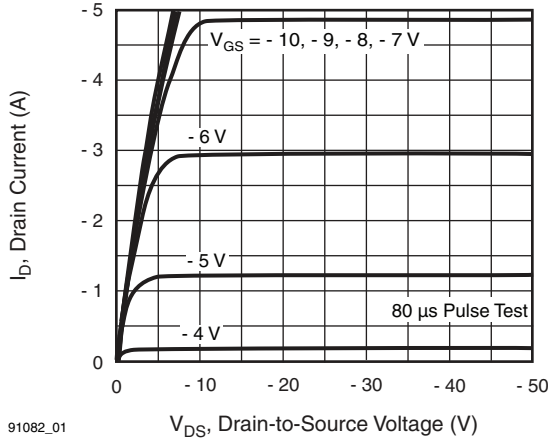
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.50	-	
Maximum junction-to-case (drain)	R_{thJC}	-	3.1	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX. UNIT	
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$		-200	-	- V	
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = -1\text{ mA}$		-	-0.22	- $V/^\circ\text{C}$	
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$		-2.0	-	-4.0 V	
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100\text{ nA}$	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -200\text{ V}, V_{GS} = 0\text{ V}$		-	-	-100 μA	
		$V_{DS} = -160\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	-500 μA	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$	$I_D = -1.5\text{ A}^b$	-	-	1.5 Ω	
Forward transconductance	g_{fs}	$V_{DS} = -50\text{ V}, I_D = -1.5\text{ A}^b$		1.0	-	- S	
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5		-	350	-	
Output capacitance	C_{oss}			-	100	-	pF
Reverse transfer capacitance	C_{rss}			-	30	-	
Total gate charge	Q_g	$V_{GS} = -10\text{ V}$	$I_D = -4.0\text{ A}, V_{DS} = -160\text{ V}$, see fig. 11 and 18 ^b	-	-	22	
Gate-source charge	Q_{gs}			-	-	12	nC
Gate-drain charge	Q_{gd}			-	-	10	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -100\text{ V}, I_D = -1.5\text{ A}, R_g = 50\text{ }\Omega, R_D = 67\text{ }\Omega$, see fig. 17 ^b		-	15	-	
Rise time	t_r			-	25	-	ns
Turn-off delay time	$t_{d(off)}$			-	20	-	
Fall time	t_f			-	15	-	
Gate input resistance	R_g	$f = 1\text{ MHz}$, open drain		0.9	-	5.7 Ω	
Internal drain inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	
Internal source inductance	L_S			-	7.5	-	nH
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p-n junction diode 		-	-	-3.5	
Pulsed diode forward current ^a	I_{SM}			-	-	-14	A
Body diode voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = -3.5\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	-7.0 V	
Body diode reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = -3.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	300	450 ns	
Body diode reverse recovery charge	Q_{rr}			-	1.9	2.9 μC	
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

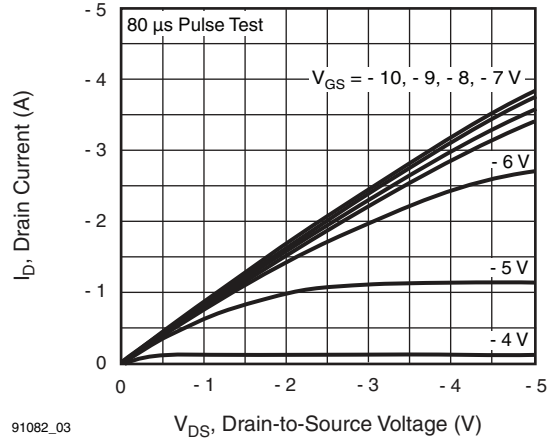
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



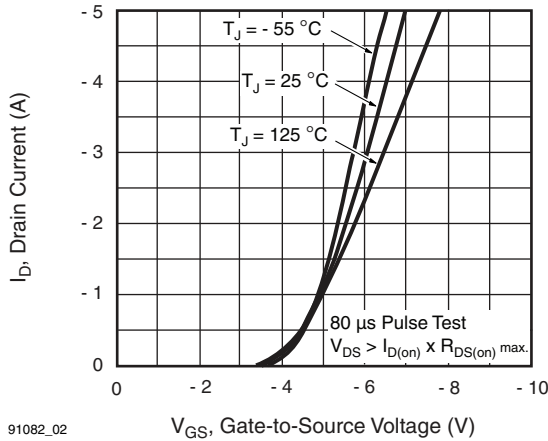
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Fig. 1 - Typical Output Characteristics



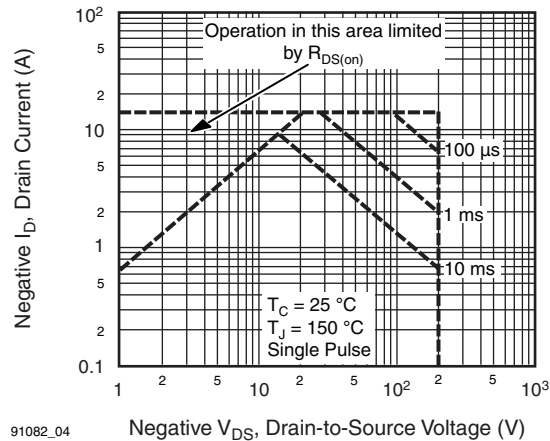
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Fig. 3 - Typical Saturation Characteristics



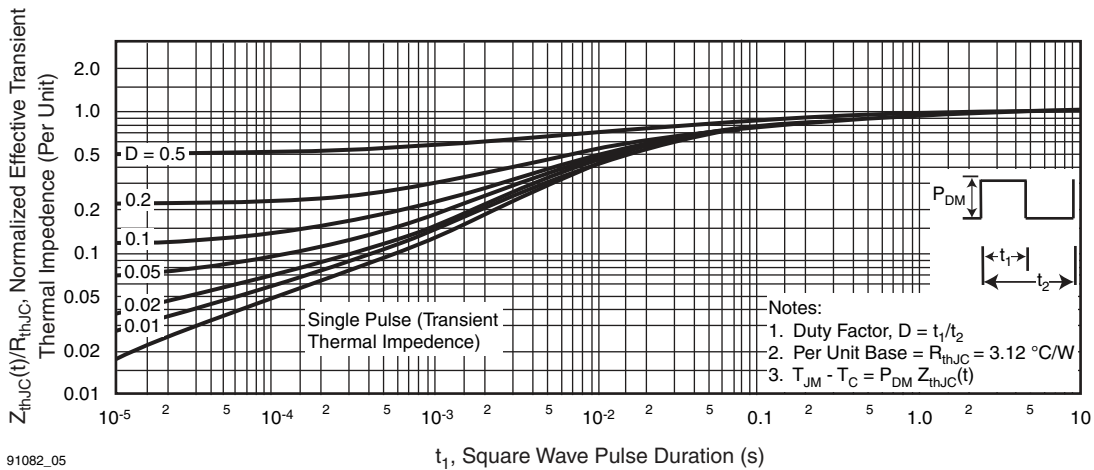
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Fig. 2 - Typical Transfer Characteristics



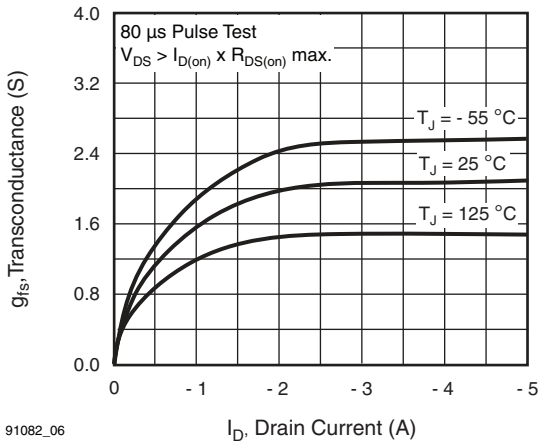
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Fig. 4 - Maximum Safe Operating Area



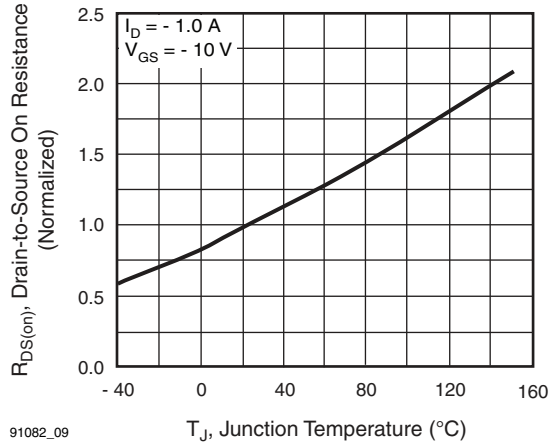
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Fig. 5 - Maximum Effective Transient Thermal Impedance, Junction-to-Case vs. Pulse Duration



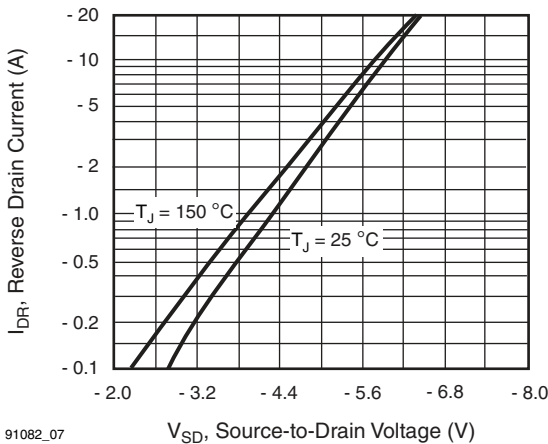
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Fig. 6 - Typical Transconductance vs. Drain Current



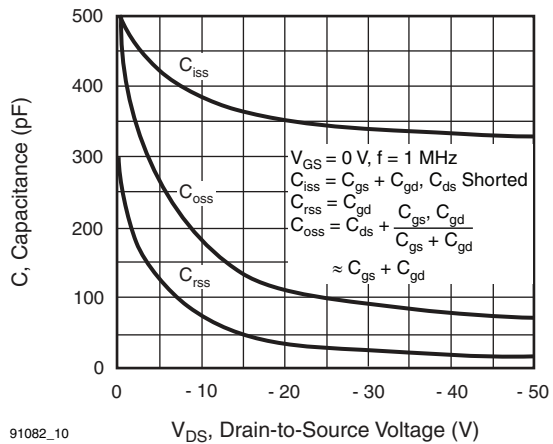
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Fig. 9 - Normalized On-Resistance vs. Temperature



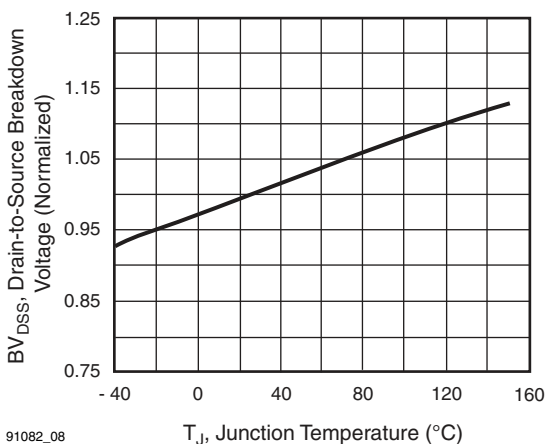
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



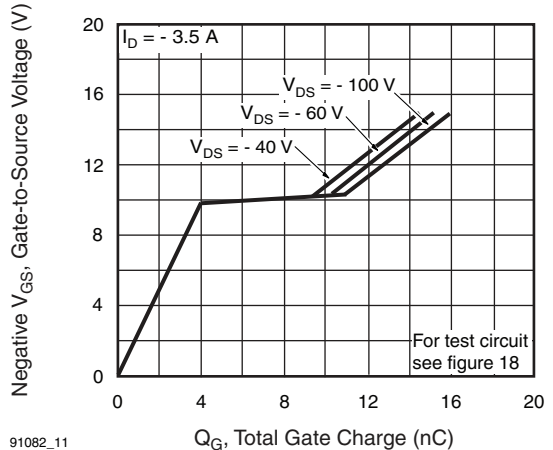
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Fig. 10 - Typical Capacitance vs. Drain-to-Source Voltage



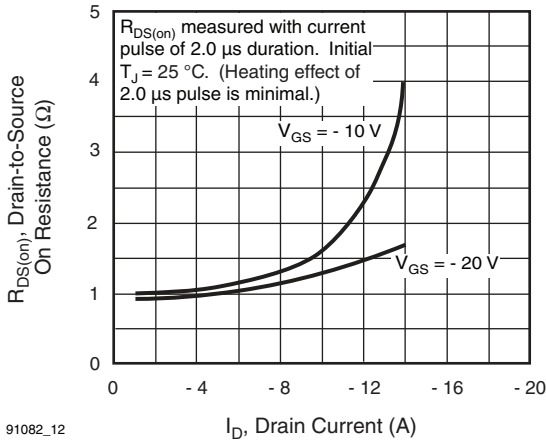
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Fig. 8 - Breakdown Voltage vs. Temperature



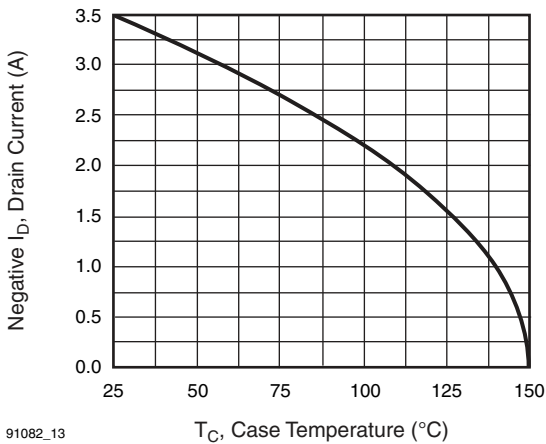
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Fig. 11 - Typical Gate Charge vs. Gate-to-Source Voltage



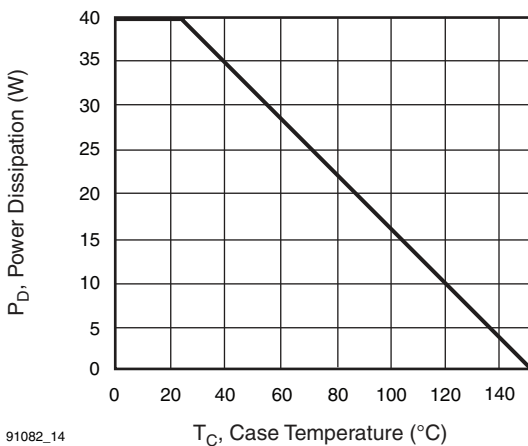
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Fig. 12 - Typical On-Resistance vs. Drain Current



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Fig. 13 - Maximum Drain Current vs. Case Temperature



91082_14

Fig. 14 - Power vs. Temperature Derating Curve

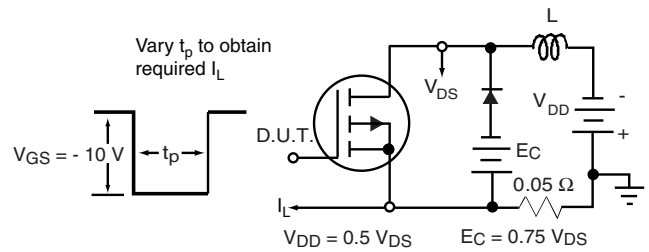


Fig. 15 - Clamped Inductive Test Circuit

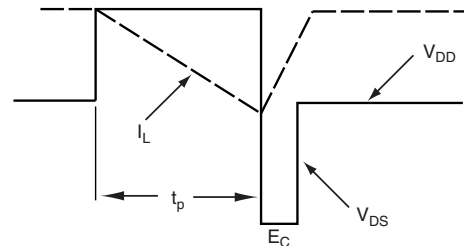


Fig. 16 - Clamped Inductive Waveforms

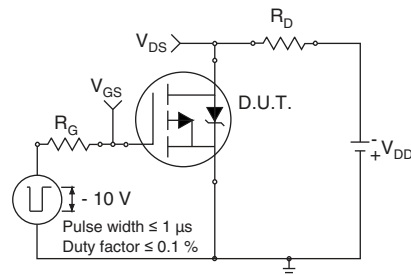


Fig. 17a - Switching Time Test Circuit

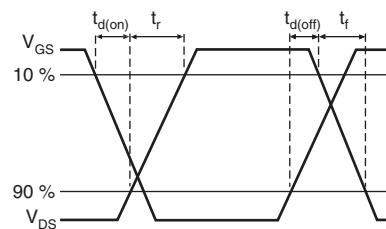


Fig. 17b - Switching Time Waveforms

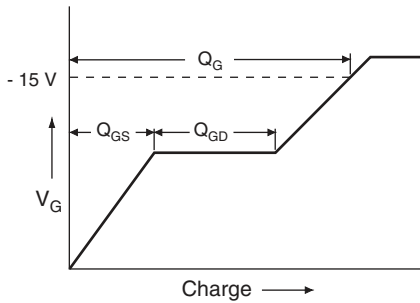


Fig. 18a - Basic Gate Charge Waveform

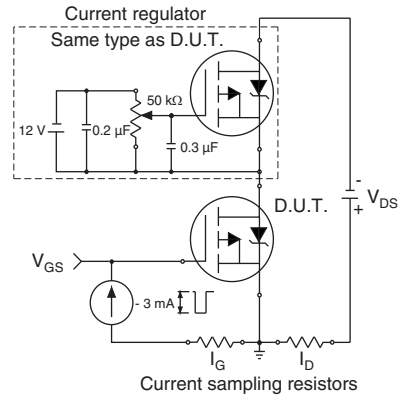


Fig. 18b - Gate Charge Test Circuit

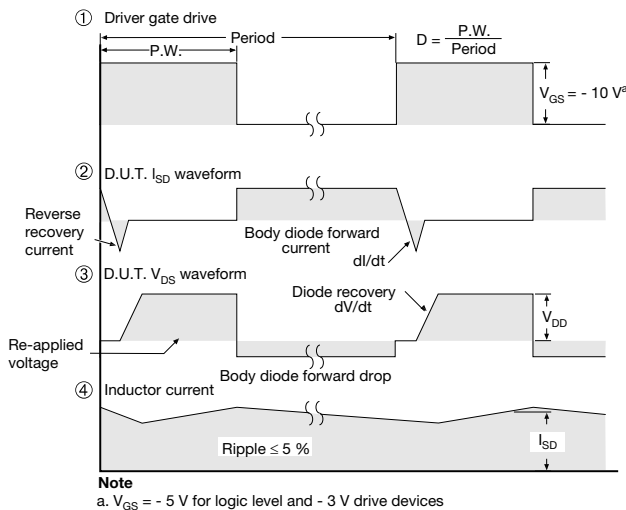
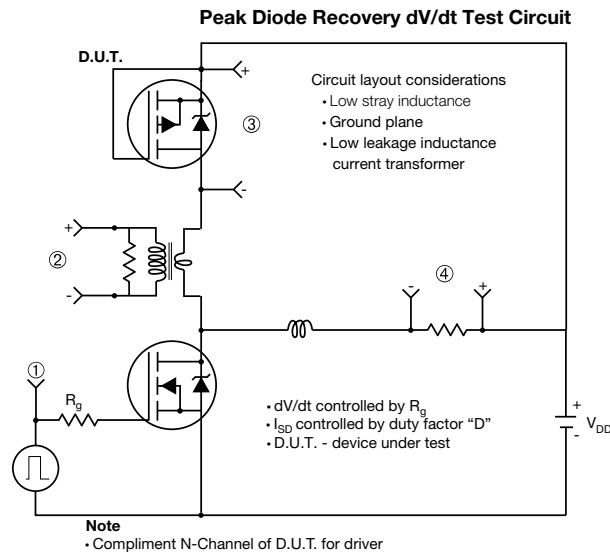


Fig. 19 - For P-Channel

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